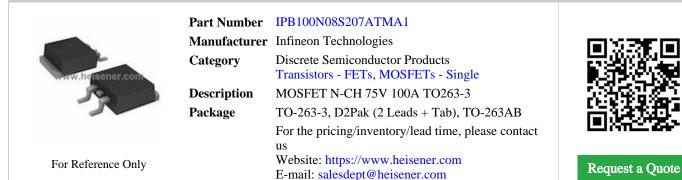


## IPB100N08S207ATMA1

#### IPB100N08S207ATMA1 Information



### **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



### IPB100N08S207ATMA1 Specifications

Manufacturer Part Number	IPB100N08S207ATMA1	
Manufacturer	Infineon Technologies	
Category	Discrete Semiconductor Products	
	Transistors - FETs, MOSFETs - Single	
Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	
Series	OptiMOS?	
FET Type	N-Channel	
Technology	MOSFET (Metal Oxide)	
Drain to Source Voltage (Vdss)	75V	
Current - Continuous Drain (Id) @ 25°C	100A (Tc)	
Drive Voltage (Max Rds On, Min Rds On)	10 <b>V</b>	
Vgs(th) (Max) @ Id	4V @ 250µA	
Gate Charge (Qg) (Max) @ Vgs	200nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds	4700pF @ 25V	
Vgs (Max)	±20V	
FET Feature	-	
Power Dissipation (Max)	300W (Tc)	
Rds On (Max) @ Id, Vgs	6.8 mOhm @ 80A, 10V	
Operating Temperature	-55°C ~ 175°C (TJ)	
Mounting Type	Surface Mount	
Supplier Device Package	PG-TO263-3-2	
Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	
		Report errors?

#### IPB100N08S207ATMA1 Guarantees



**Quality Guarantees** 

We provide 90 days warranty. \* If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

# SERVICE BUARANTEE

#### Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

#### IPB100N08S207ATMA1 Payment Methods



If you have any question about IPB100N08S207ATMA1, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com